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## NTE2322

### Silicon PNP Transistor Quad, General Purpose

**Absolute Maximum Ratings:**

Collector–Emitter Voltage, $V_{CEO}$ .....	40V
Collector–Base Voltage, $V_{CBO}$ .....	60V
Emitter–Base Voltage, $V_{EBO}$ .....	5V
Continuous Collector Current, $I_C$ .....	600mA
Total Device Dissipation ( $T_A = +25^\circ\text{C}$ , Each Transistor), $P_D$ .....	0.65W
Derate Above $25^\circ\text{C}$ .....	6.5mW/ $^\circ\text{C}$
Total Device Dissipation ( $T_A = +25^\circ\text{C}$ , Total Device), $P_D$ .....	1.9W
Derate Above $25^\circ\text{C}$ .....	19mW/ $^\circ\text{C}$
Operating Junction Temperature Range, $T_J$ .....	$-55^\circ$ to $+125^\circ\text{C}$
Storage Temperature Range, $T_{stg}$ .....	$-55^\circ$ to $+125^\circ\text{C}$
Thermal Resistance, Junction–to–Ambient, $R_{thJA}$ .....	66 $^\circ\text{C}/\text{W}$

**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>OFF Characteristics</b>						
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10\text{mA}$ , $I_B = 0$ , Note 1	40	–	–	V
Collector–Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}$ , $I_E = 0$	60	–	–	V
Emitter–Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}$ , $I_C = 0$	5	–	–	V
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 30\text{V}$ , $I_E = 0$	–	–	50	nA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 3\text{V}$ , $I_E = 0$	–	–	50	nA
<b>ON Characteristics (Note 1)</b>						
DC Current Gain	$h_{FE}$	$V_{CE} = 10\text{V}$ , $I_C = 10\text{mA}$	75	–	–	
		$V_{CE} = 10\text{V}$ , $I_C = 150\text{mA}$	100	–	–	
		$V_{CE} = 10\text{V}$ , $I_C = 300\text{mA}$	30	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 150\text{mA}$ , $I_B = 15\text{mA}$	–	–	0.4	V
		$I_C = 300\text{mA}$ , $I_B = 30\text{mA}$	–	–	1.6	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 150\text{mA}$ , $I_B = 15\text{mA}$	–	–	1.5	V
		$I_C = 300\text{mA}$ , $I_B = 30\text{mA}$	–	–	2.6	V

Note 1. Pulse test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .

**Electrical Characteristics (Cont'd):** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Small-Signal Characteristics</b>						
Current Gain-Bandwidth Product	$f_T$	$V_{CE} = 20\text{V}, I_C = 50\text{mA}, f = 100\text{MHz}$	200	–	–	MHz
Output Capacitance	$C_{obo}$	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$	–	–	8	pF
Input Capacitance	$C_{ibo}$	$V_{EB} = 2\text{V}, I_C = 0, f = 1\text{MHz}$	–	–	30	pF

**Pin Connection Diagram**

